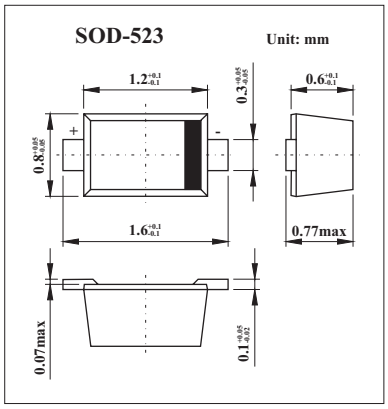
Silicon Schottky Barrier Diode

HSC226



Features

- Low reverse current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	25	V
Non-Repetitive peak forward surge current	I_{FSM}*	200	mA
Forward current	I_F	50	mA
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Note

10ms Sinewave 1pulse

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 1 mA			0.33	V
		I_F = 5 mA			0.38	
Reverse current	I_R	V_R = 20 V			0.45	μ A
Capacitance	C	V_R =1 V, f = 1 MHz			2.80	pF

Marking

Marking	S4